

## **Quarterly Reliability Monitoring Results**

## Quarters: Q1/2021 to Q4/2021

Based on structural similarity

Supplier Nexperia B.V.		User Part Number						
		BC55-10PAS						
Name of Laboratory  Assembly reliability labs  Based on AEC-Q101 Test		Part Description						
		Nexperia DHAM Small Signal Bipolar Transistor						
		MCD package						
		Test Conditions	Duration	# Lots	# Quantity	# Rejects		
	TEST							
	Pre- and Post-Stress							
# E1	Electrical Test	Tamb = 25 °C	N/A	see below	all parts	see below		
		JESD22-A113						
		Bake Tamb = 125 °C	24 hours					
	PC Decemblished	Soak Tamb = 85 °C, RH = 85%	168 hours			_		
# A1	Preconditioning	Reflow soldering	3 cycles	208	16640	0		
		MIL-STD-750-1						
	HTRB	M1039 Method A						
		Tj = Tjmax, Vr = 100% of max. datasheet reverse voltage				_		
# B1	Bias	reverse voltage	1000 hours	202	16160	0		
	тс	JESD22-A104						
# 04	Temperature Cycling	-65 °C to Timax, not to exceed 150°C	1000 eveles	52	4160	0		
# A4	remperature Cycling	,	1000 cycles	52	4160	U		
	AC	JESD22-A102 Tamb = 121 °C, RH = 100 %						
# A3 alt	Autoclave	Pressure = 205 kPa (29.7 psia)	96 hours	52	4160	0		
# A3 all	Addedave	11635d16 = 203 Kt d (23.7 p3id)	90 110015	32	4100	U		
	H3TRB	JESD22-A101						
	High Humidity High	Tamb = 85 °C, RH = 85%, VR = 80 % of						
# A2 alt	Temperature Reverse Bias		1000 hours	52	4160	0		
# AZ alt	remperature neverse slas	MIL-STD-750 Method 1037	1000 110015	32	4100	0		
	IOL	ton = toff, devices powered to insure $\Delta T_i$ =						
# A5	Intermittent Operating Life		1000 hours	52	4160	0		
# A3	zazzanie operacing Life	2.2. 2.3. 2000 0,000	1000 110015	JZ	4100	U		
	RSH	JESD22-A111						
# C8	Resistance to Solder Heat	260 °C ± 5 °C	10 s	n.a.	n.a.	n.a.		
	SD		100					
# C10	Solderability	J-STD-002		111	1110	0		

<sup>[1]</sup> The maximum applied voltage is limited by test chamber set up and does not exceed 115V.

## **Calculation of FIT and MTTF**

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB, Test #B1)
Confidence level 60%, derated to 55 °C, activation energy 0.7 eV, test time 168 to 1000 hours

Wafer Fab	Technology	Quantity	Rejects	Failure Rate (FIT)	MTTF (hrs)
Nexperia	Small Signal Bipolar				
DHAM	Transistor	16160	0	0.26	3.81E+09

© 2022 Nexperia B.V.

All information hereunder is per Nexperia's best knowledge. This document does not provide for any representation or warranty express or implied by Nexperia. In case Nexperia has tested the product, this documentation reflects the outcome of the analysis of the actually tested parts only.

nexperia.com